

ABSTRACT

A semiconductor device includes an active pattern which includes a lower pattern extending in a first direction, and sheet patterns spaced apart from the lower pattern in a second direction perpendicular to an upper surface of the lower pattern, each sheet pattern including an upper surface and a lower surface, a gate structure disposed on the lower pattern and including a gate electrode and a gate insulating film, the gate electrode and the gate insulating film surrounding each sheet pattern, and a source/drain pattern disposed on at least one side of the gate structure. The gate structure includes inter-gate structures that are disposed between the lower pattern and a lowermost sheet pattern and between two sheet patterns, and contacts the source/drain pattern. The gate insulating film includes a horizontal portion with a first thickness, and a first vertical portion with a second thickness different from the first thickness.

FIG. 2